

Experience with CNM 3D sensors
for the ATLAS IBL
9th Trento Workshop

February 27th, 2014

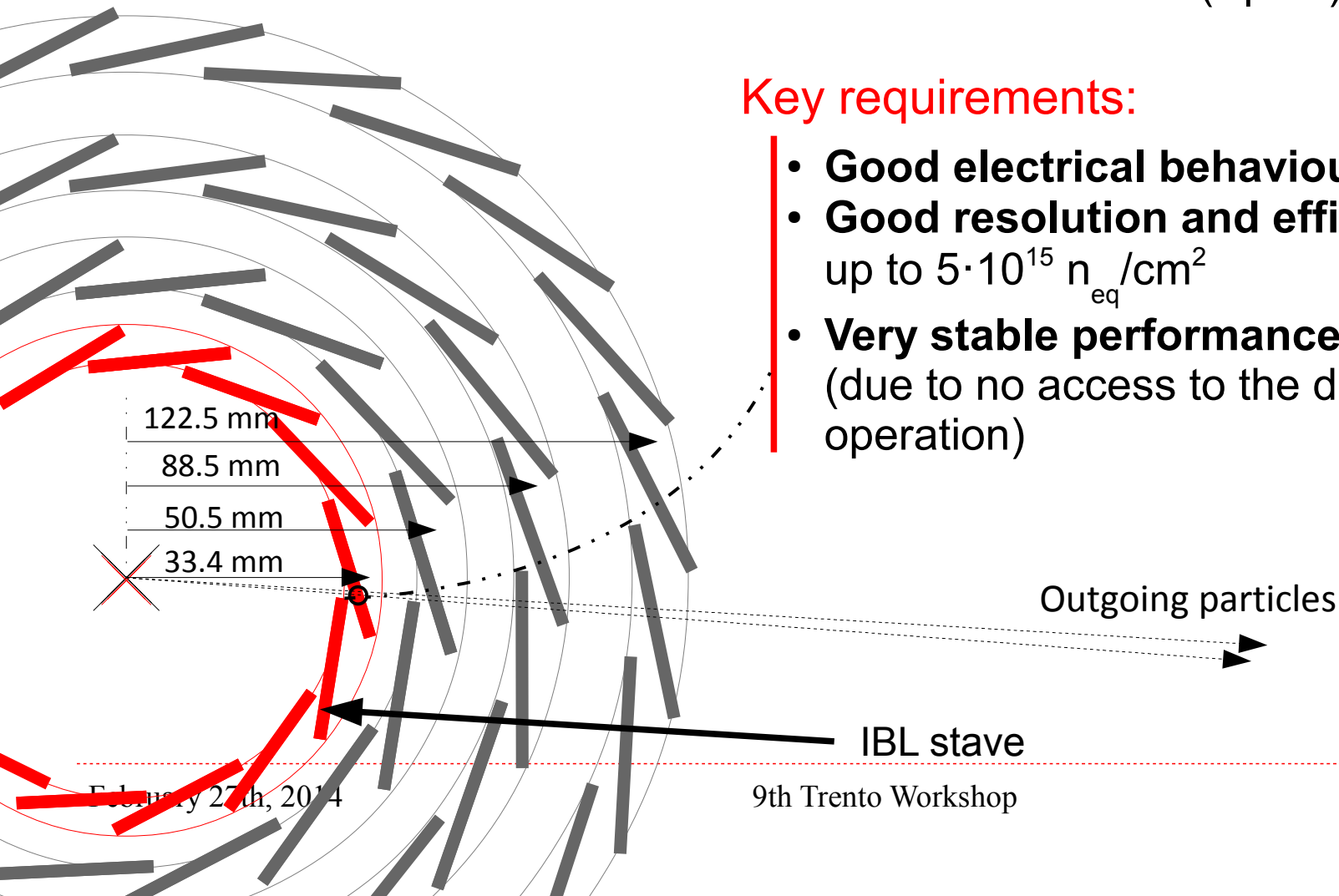
I. López,
S. Grinstein, J. Lange, A. Micelli

IFAE Insertable B-Layer

- ATLAS new layer of pixel detectors
 - ~3 cm away from the beam
 - **3D Pixel Silicon Sensors [25%]** (+ planars [75%])
 - 3D sensors fabricated at CNM (Spain) and FBK (Italy)

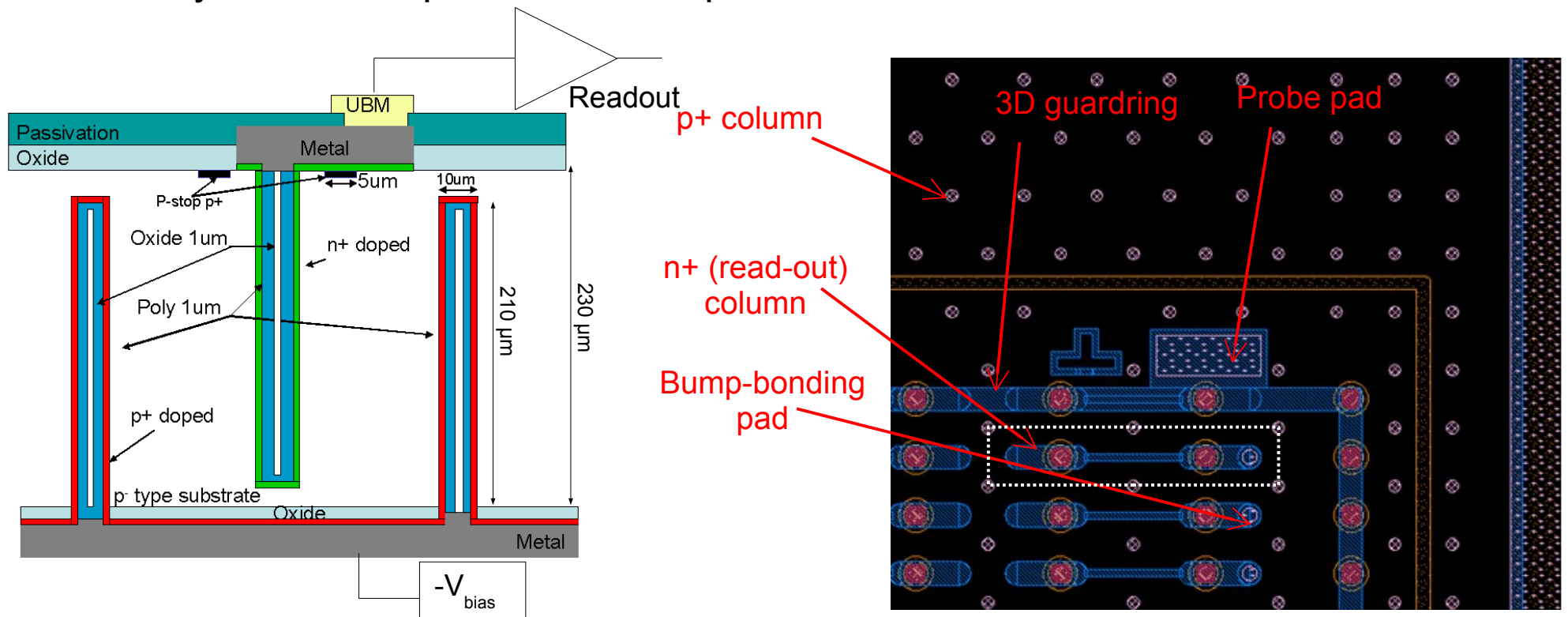
Key requirements:

- **Good electrical behaviour**
- **Good resolution and efficiency**
up to $5 \cdot 10^{15} n_{eq}/cm^2$
- **Very stable performance**
(due to no access to the detector while in operation)



IFAE^R CNM sensors in IBL

- Sensor fabricated at CNM-Barcelona and UBM'ed/flip-chipped at IZM
- Double sided process, p-bulk 230 μm thick
- 210 μm columns – **do not** fully penetrate the substrate
- 3D guard-ring with probe pad for IV measurements
- FE-I4 front-end for IBL
 - Array of 80x336 pixels, 50x250 μm^2 each

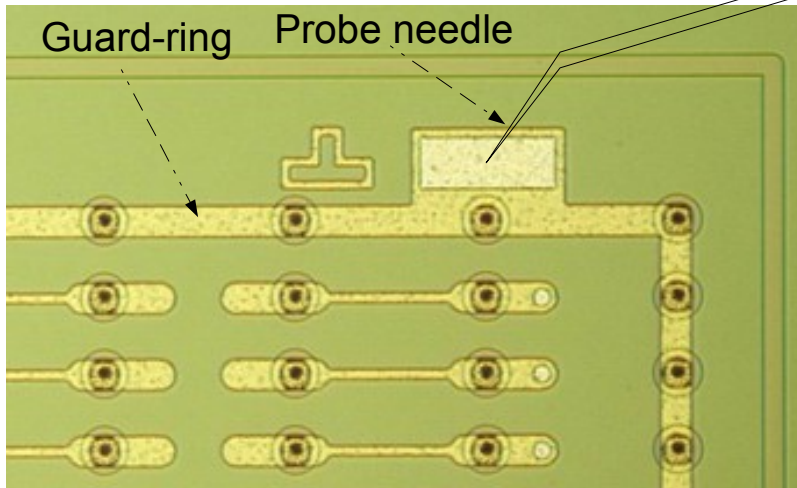


Leakage current versus bias voltage is a critical indicator of the quality of the sensor:

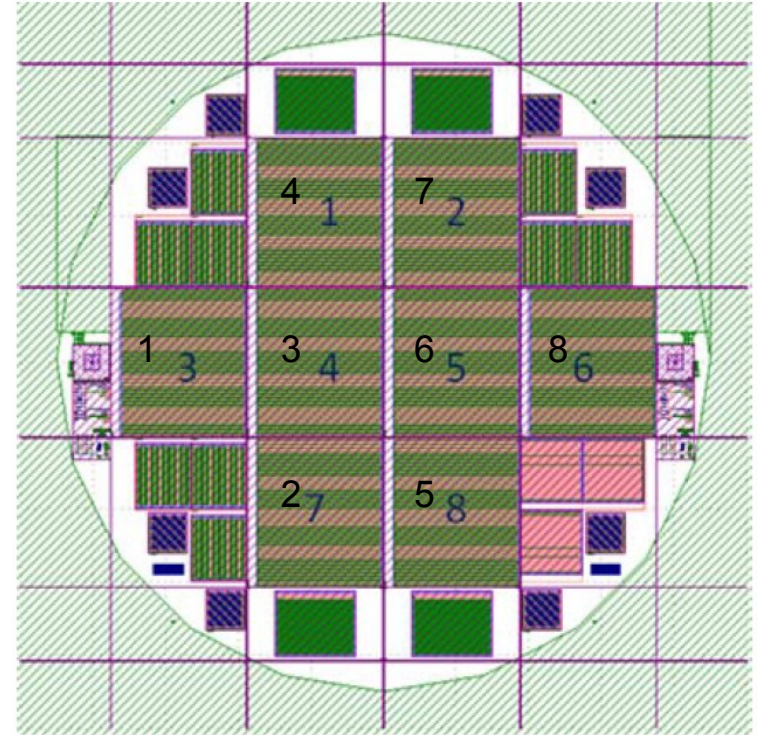
- Low breakdown prevents reaching depletion voltage
- High leakage current leads to large noise

Selection of good CNM tiles for flip-chip:

- **IV measurement through 3D guard-ring at wafer level**

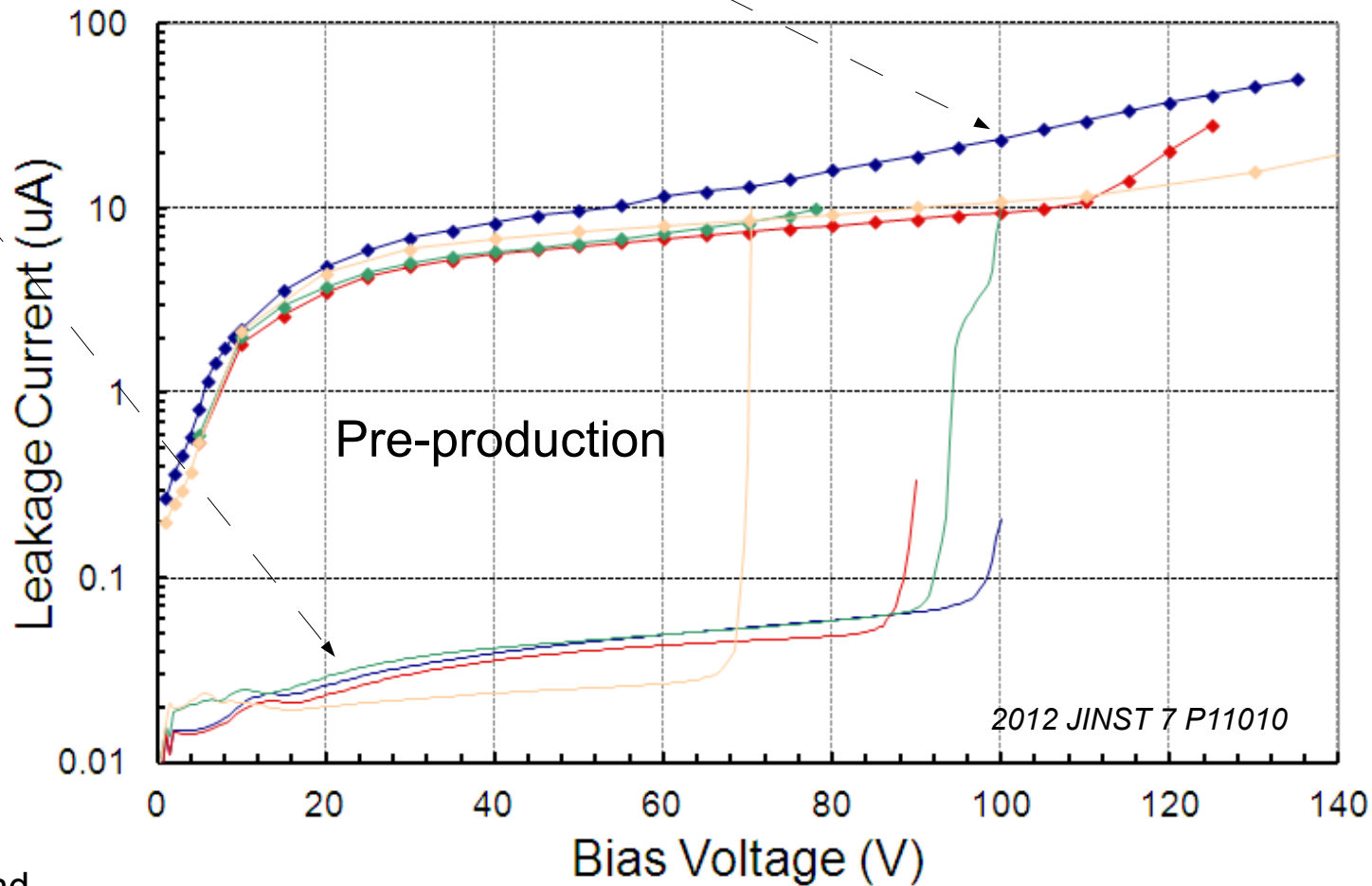


← CNM sensor IV measurement through 3D GR



- 3D guard-ring procedure was tested with pre-production run:
 - Wafer IV quality consistent with after flip-chip IVs
 (high V_{bd} sensors at wafer level* ↔ high V_{bd} sensors after flip-chip**)

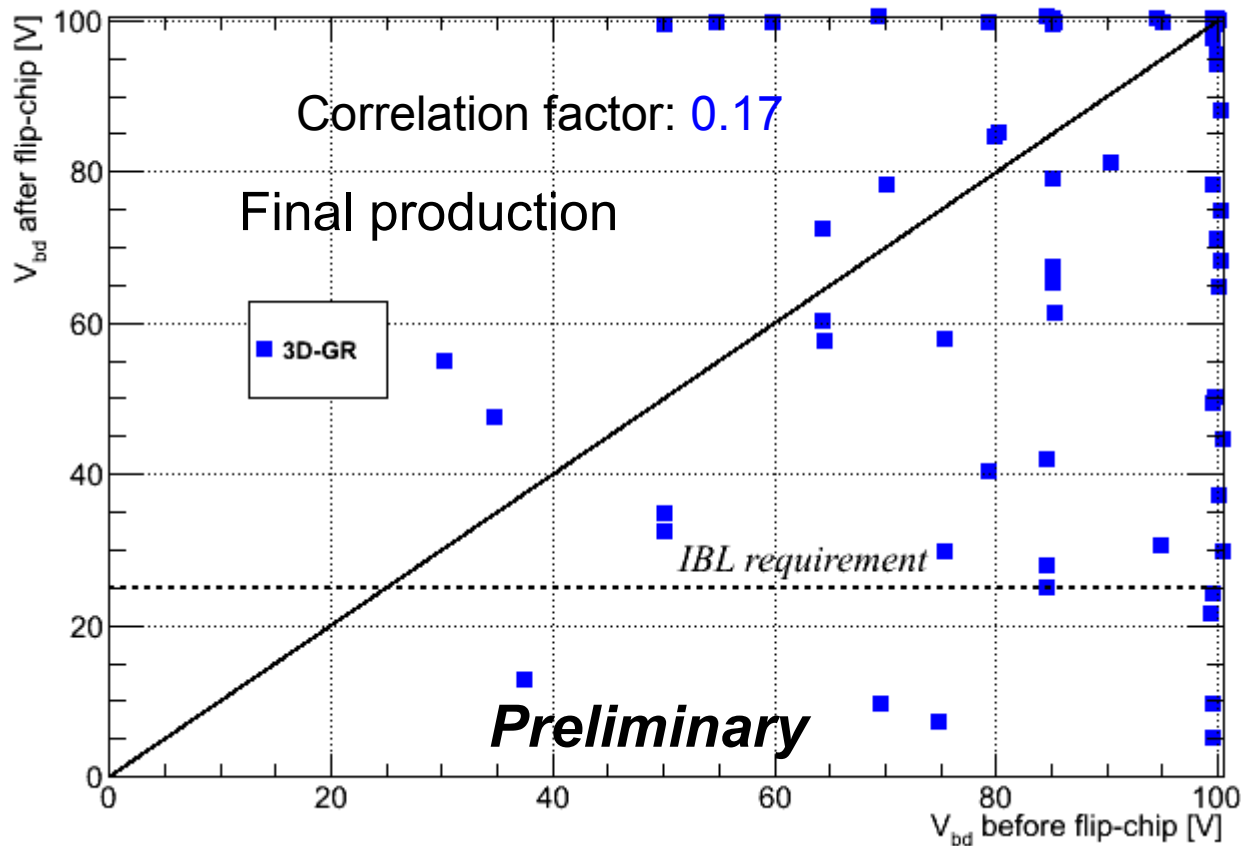
BUT:
 low statistics
 +
 only good sensors
 were tested



*i.e. measured trough 3D guardring

**i.e. measured trough front-end

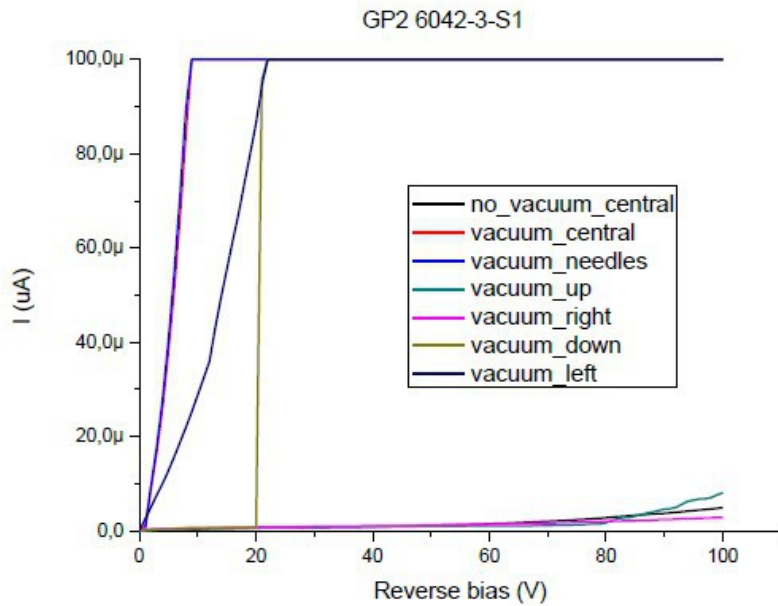
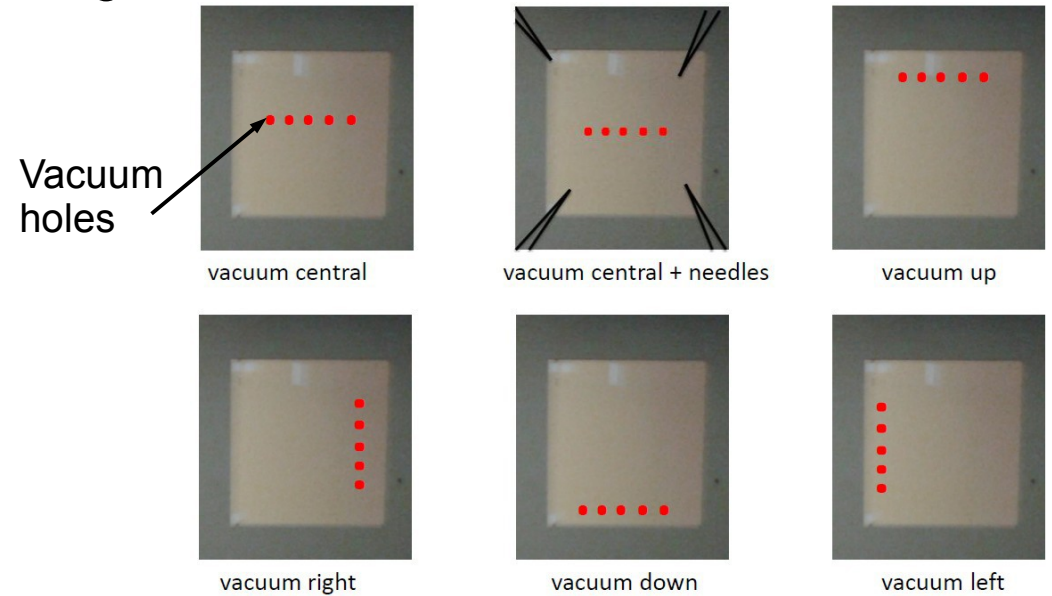
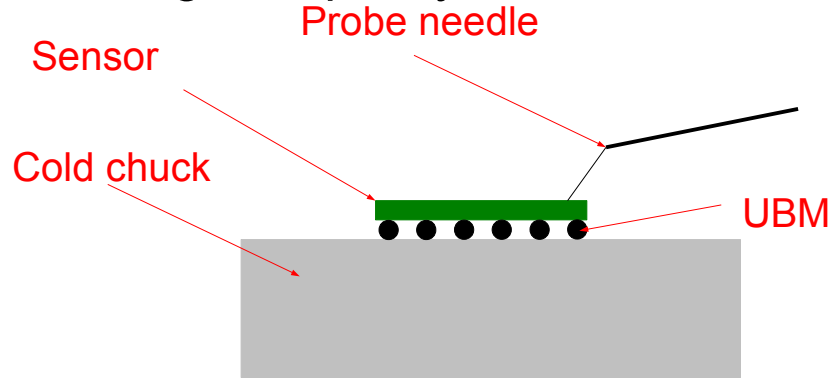
- ▶ Measured V_{bd} before (3D GR) and after flip-chipping on IBL production CNM sensors
 - Measurements show poor correlation
 - Guardring IV measurements not optimal for electrical characterisation
 - Need an alternative method to select good sensors



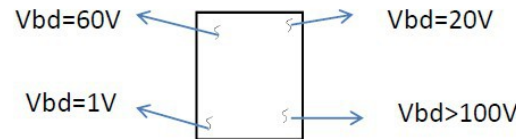
Reason:
 Only edge region bias:
 → No information about inner pixels

3D GR measurements done at CNM

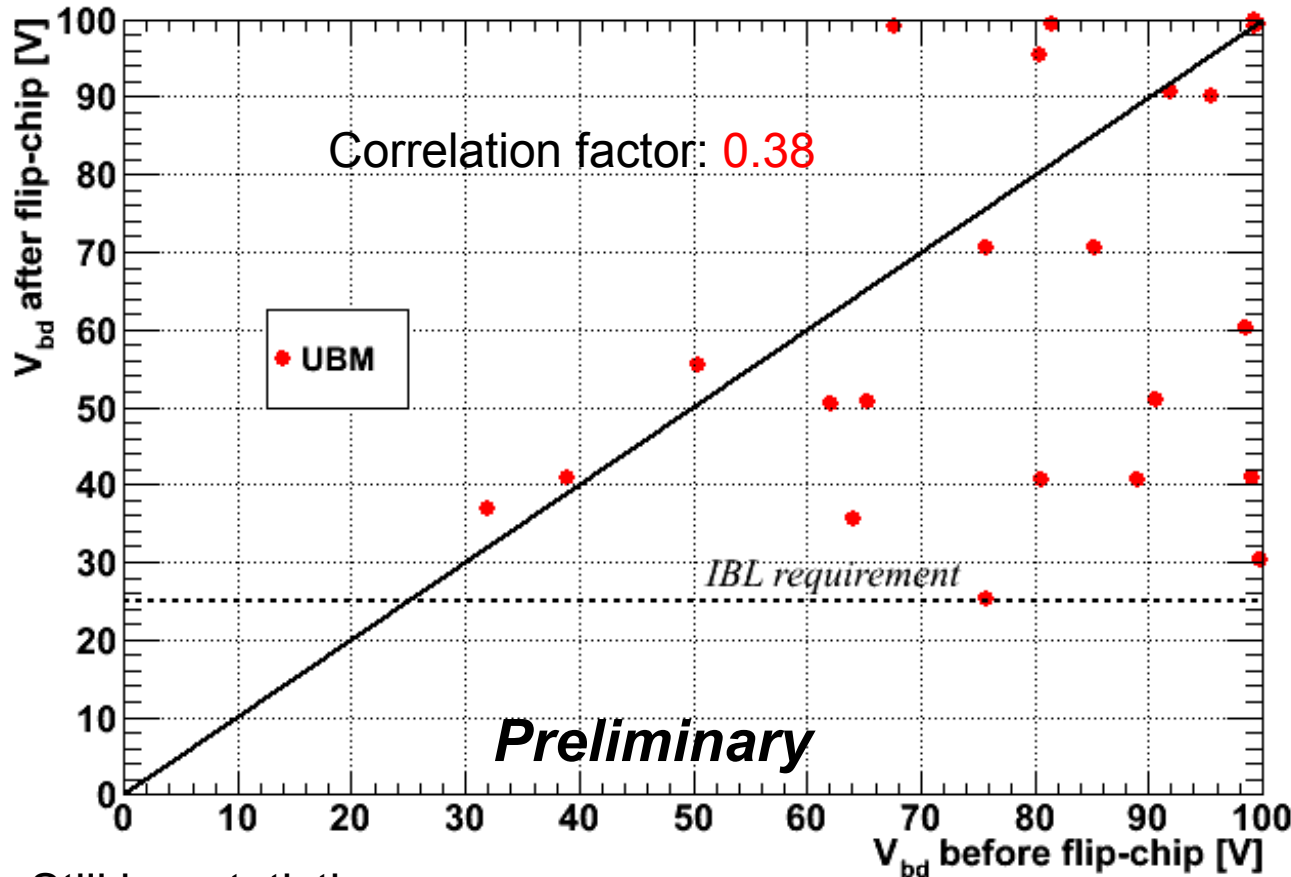
- Sensors at IZM sent sensors to CNM to redo measurements
- Select good quality sensors for IBL through **UBM**



Measure IV with sensor on different positions
→ Take the lowest V_{bd}

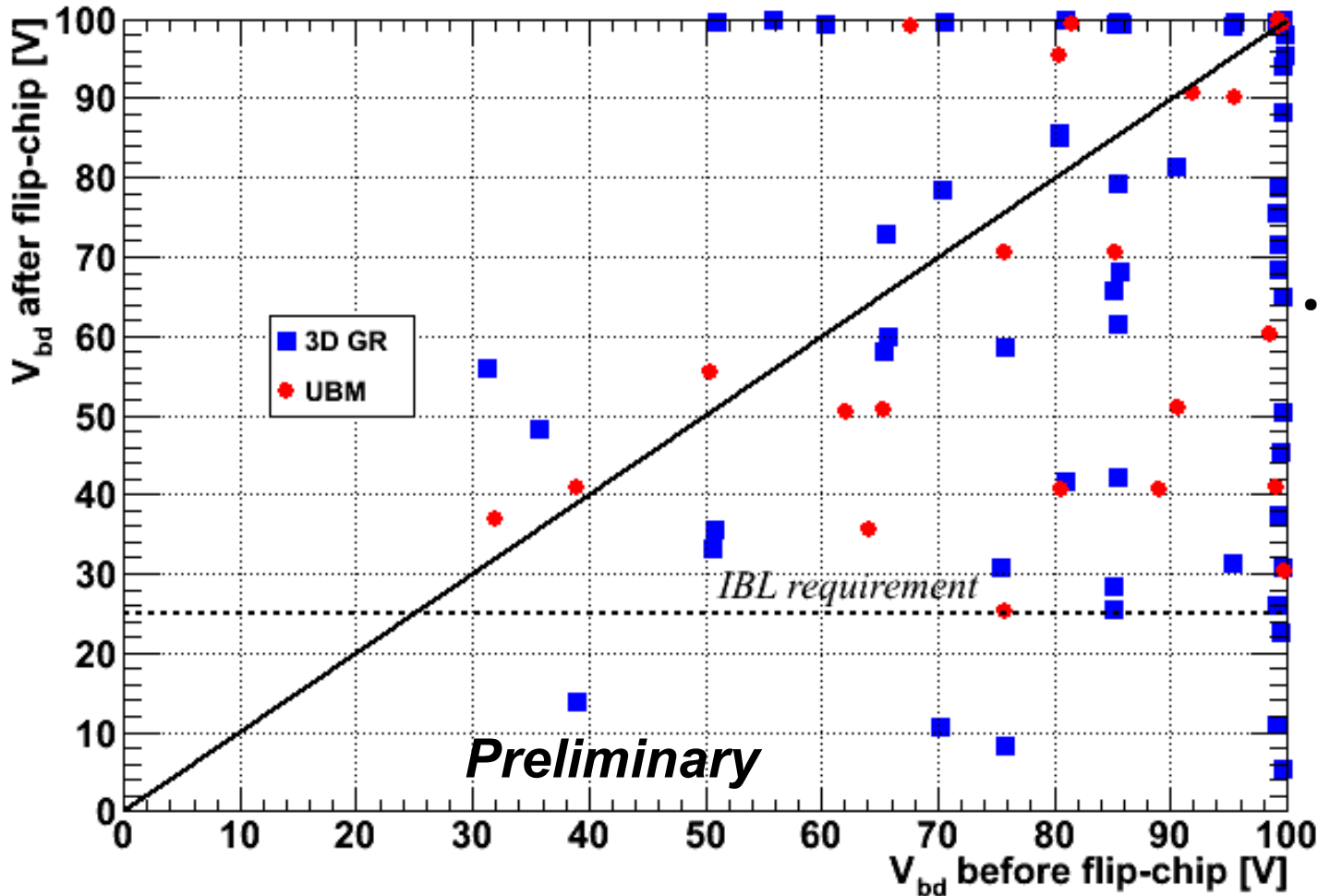


IV measurements done by **Sergi Esteban (CNM)**



IV measurements before flip-chip done by Sergi Esteban (CNM)

- Still low statistics:
 - Sensors not yet assembled/still at IZM
- Inconsistency in naming makes tracking down modules difficult...
 - Measurement procedures not entirely consistent between institutes
 - e.g. not the same current limitation
→ worsens consistency of measurements



Correlation factors:

- 3D GR: 0.17
- UBM: 0.38
- FBK*: 0.66

- UBM method is much more consistent but not as good as full sensor measurements (*a la* FBK)

See Sonia's talk for more details

* From Andrea Gaudiello

- 92 good sensors identified and sent back to IZM for flip chipping

Qualification for IBL:

→ **Goal:** Investigate efficiency with (non-) irradiated sensors

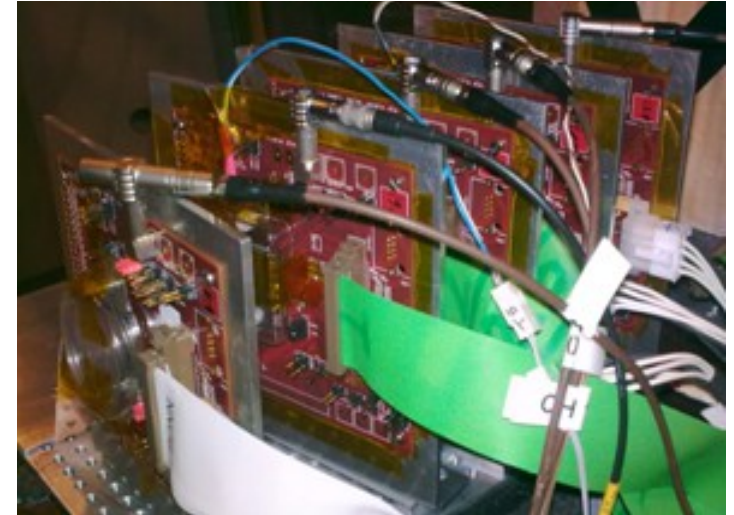
→ Test beam facilities:

- CERN: 120 GeV pions
- DESY: 4 GeV electrons

→ List of IBL testbeams with CNM samples

- April 2011 (DESY)*
- June 2011 (CERN)
- September 2011 (CERN)
- April 2012 (DESY)
- May 2012 (DESY)

*only FE-I3 CNM devices

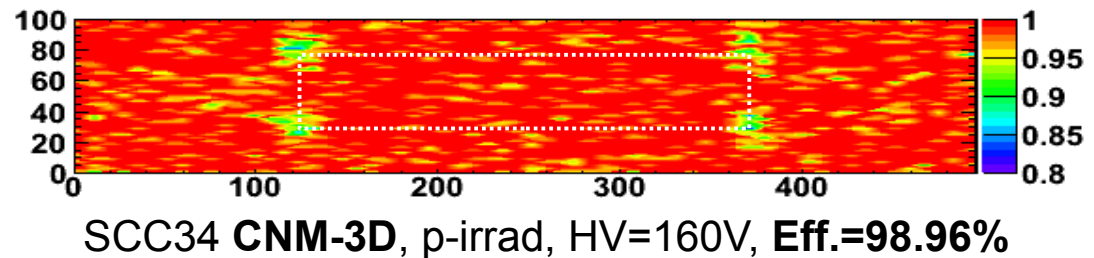
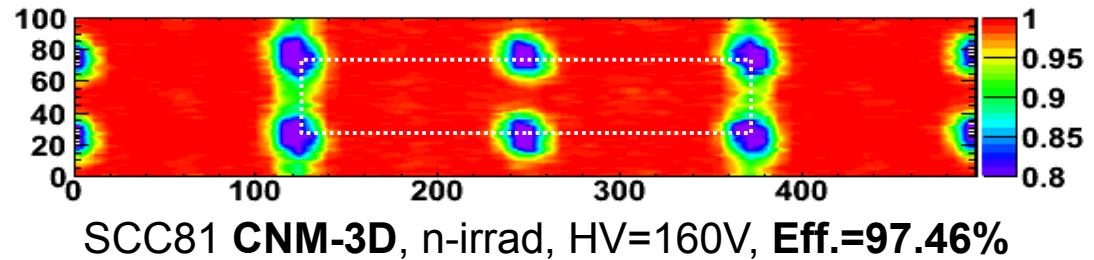
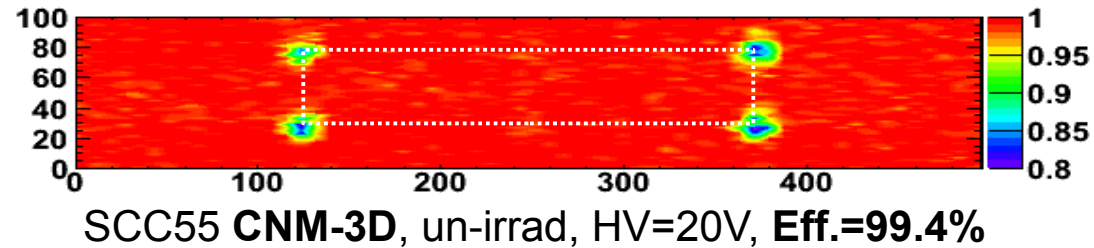


Sample	Irradiation facility	Dose [n _{eq} /cm ²]	Testbeam
CNM34	KIT (p)	5·10 ¹⁵	June+Sept 2011 (CERN), April 2012 (DESY)
CNM36	KIT (p)	6·10 ¹⁵	May 2012 (DESY)
CNM55	Un-irrad	–	June+Sept 2011 (CERN), April 2012 (DESY)
CNM81	TRIGA (n)	5·10 ¹⁵	Sept 2011 (CERN)
CNM82	TRIGA (n)	5·10 ¹⁵	June 2011 (CERN)
CNM97	KIT (p)	5·10 ¹⁵	June 2011 (CERN)

IFAE^R Test beam results (I)

Pre-production results met IBL requirements:

- IBL CNM sensors have shown an excellent overall **efficiency**
> 97 % even after $5 \cdot 10^{15} n_{eq}/cm^2$
- Good position resolution of FE-I4A sensors have been measured:
~10 μm resolution on short pixel direction

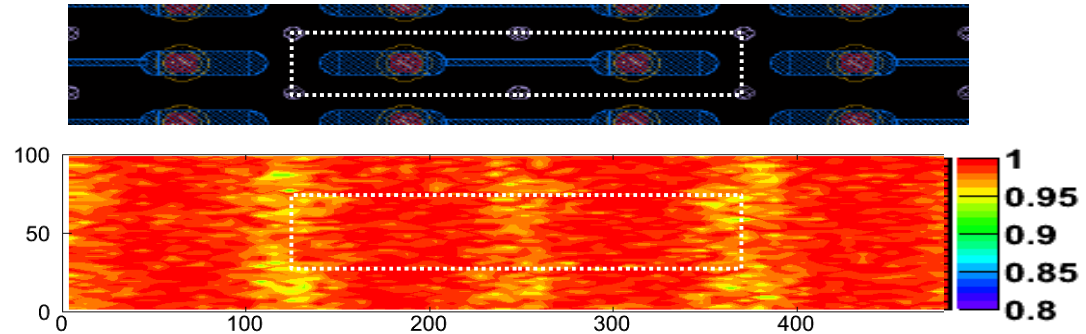


Pre-production CNM module

IFAE^R Test beam results (II)

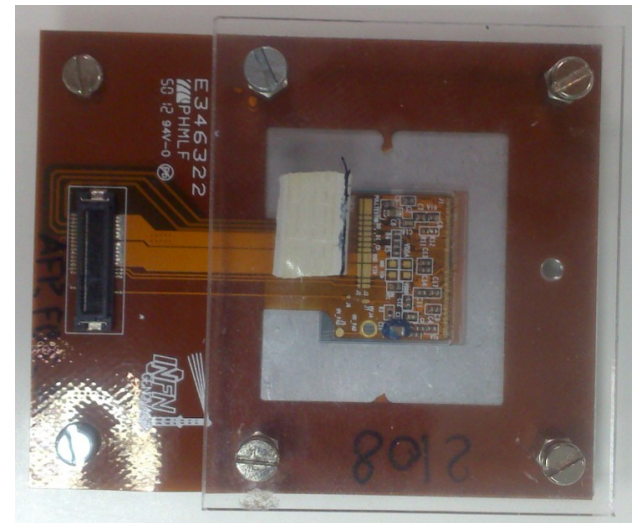
Test-beam on June 2013 at DESY with full IBL modules FE-I4B (un-irradiated)

- Results consistent with pre-production results
- > 98 % efficiency

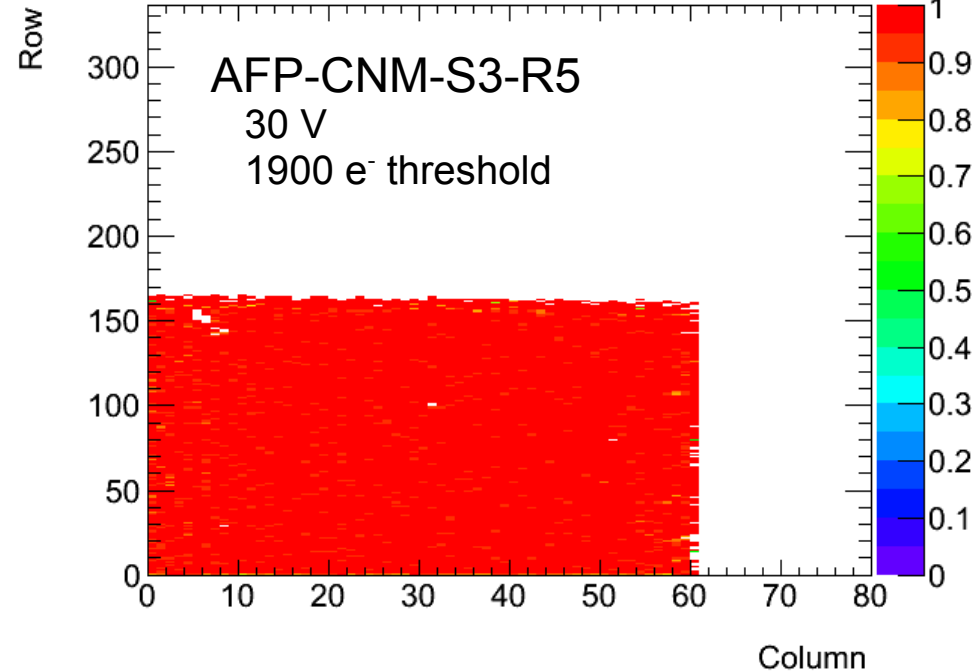


AFP-CNM-S3-R5 **CNM-3D**, un-irrad, HV=20V, **Eff.=98.3%**

Telescope resolution at DESY TB $\sim 12-17 \mu\text{m}$
→ columns not fully visible

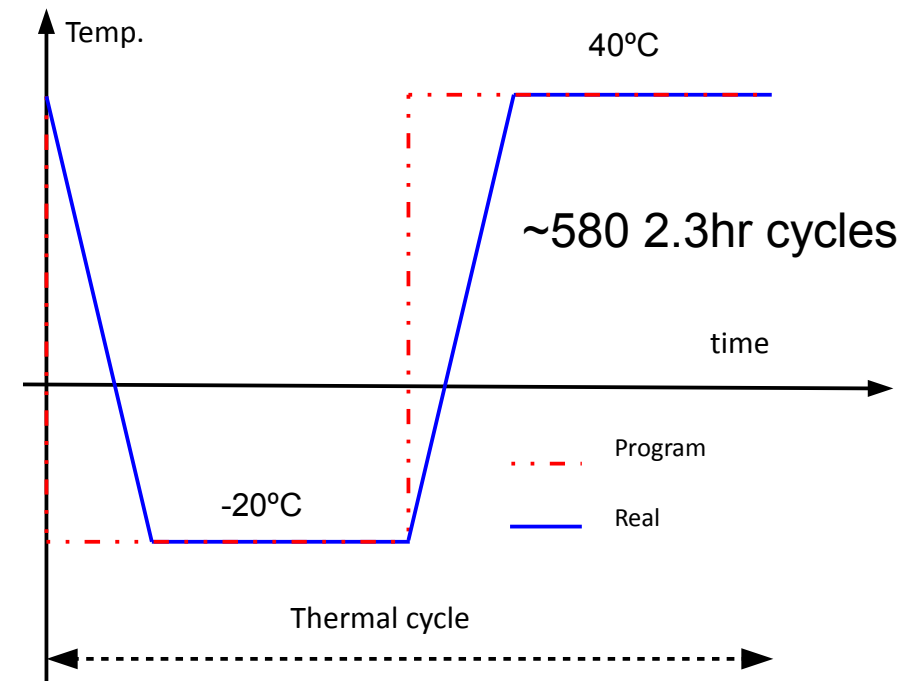
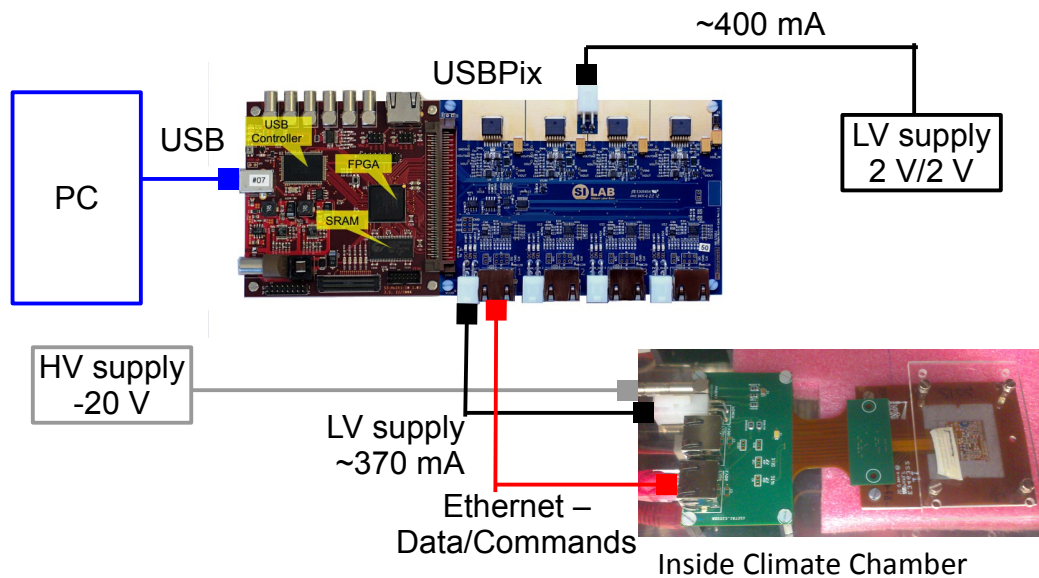


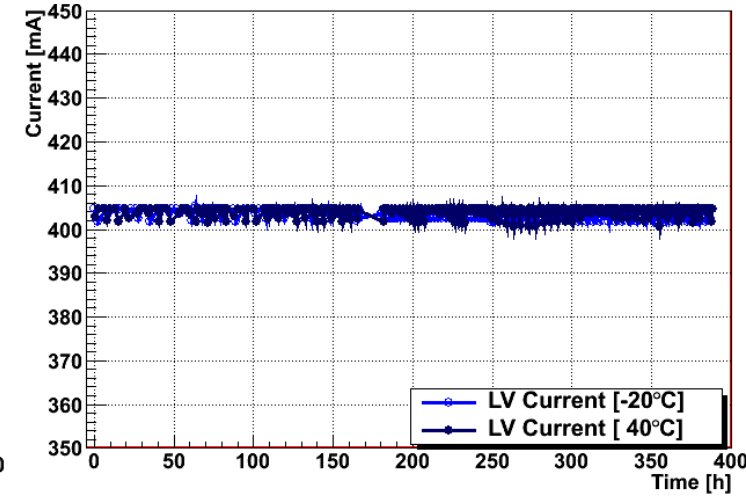
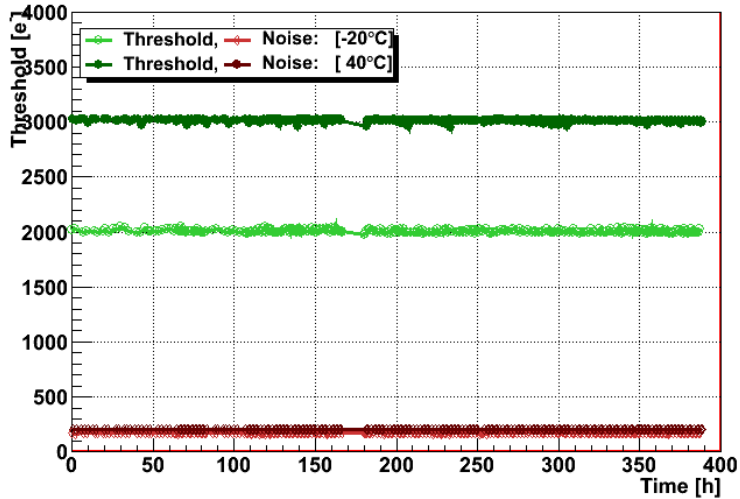
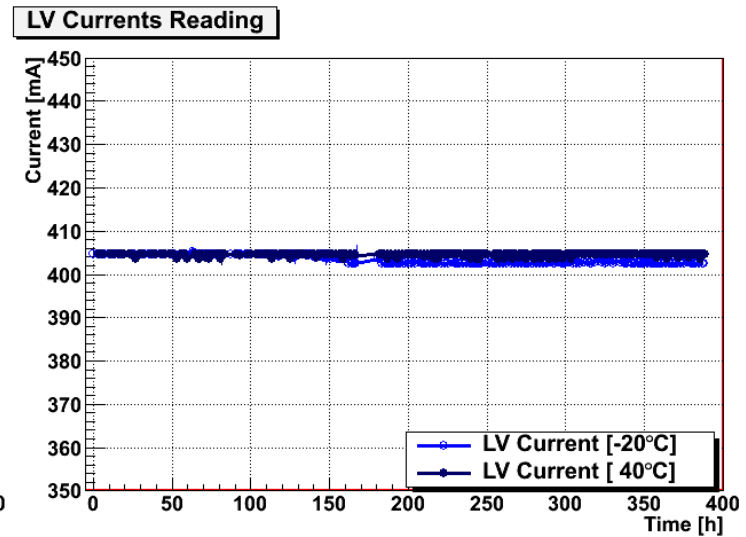
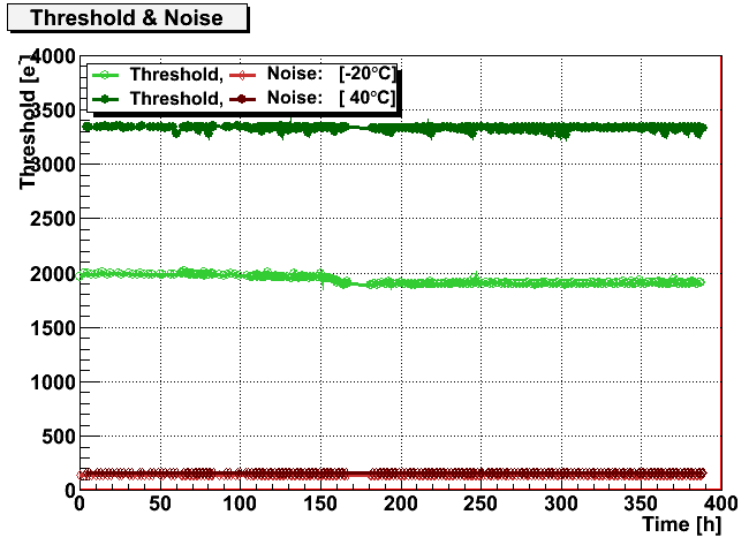
Final IBL production module



IFAE^R Ageing studies (I)

- Long term operation of devices during thermal cycles to ensure stable performance
 - 2 CNM (and 2 FBK) devices under test
 - 57 days of thermal cycle from -20 to 40°C (wider range than expected during operation)
 - Measurement performed periodically:
 - Threshold distribution
 - Noise distribution
 - ToT distribution
 - Temperature
 - LV supply current





→ Calibration parameters stable during operation

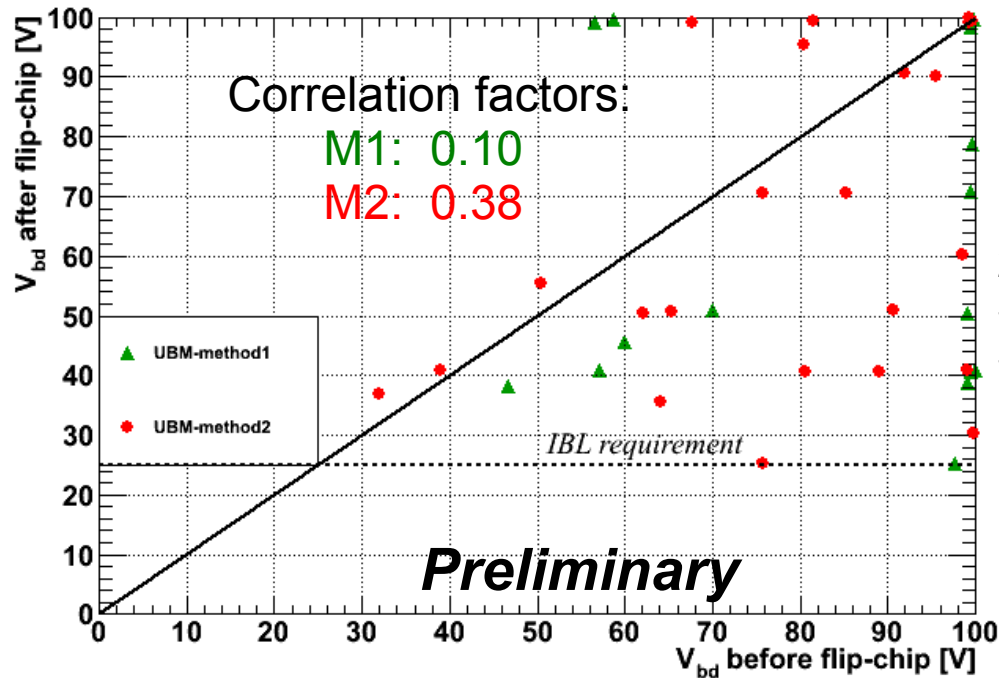
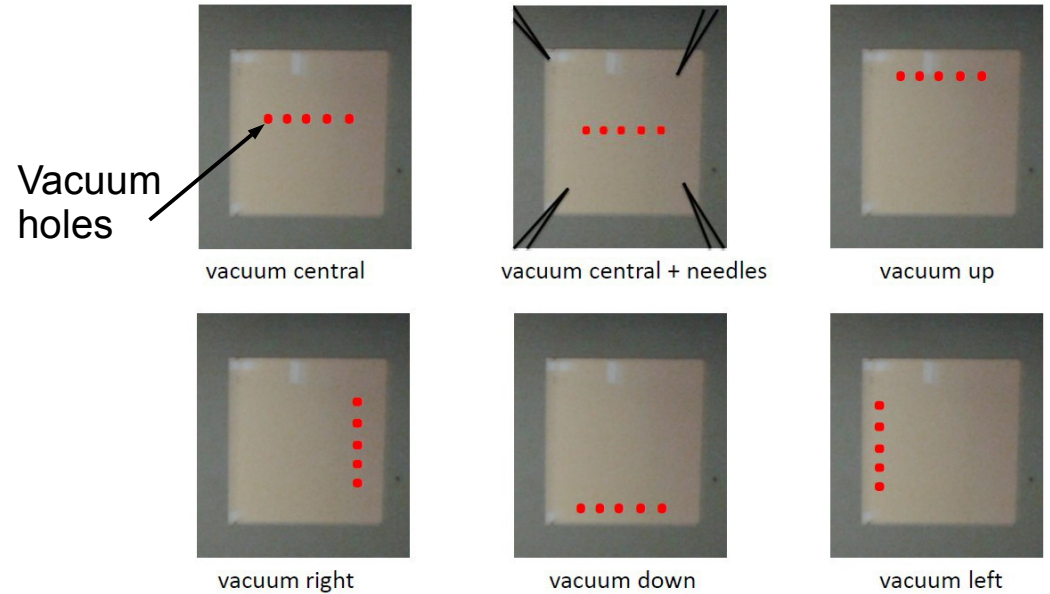
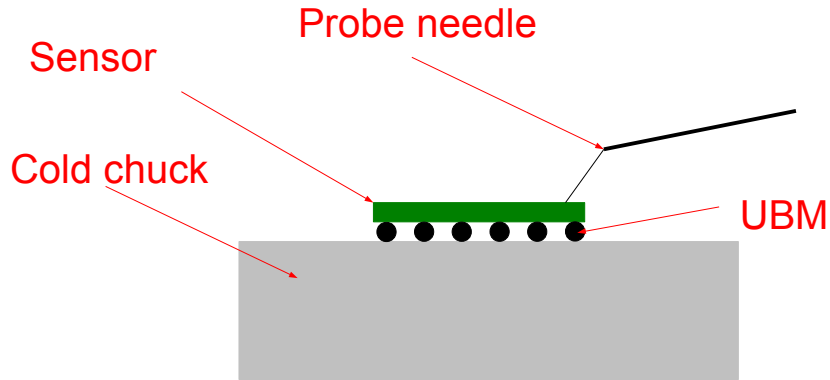
Lessons learned from IBL:

- 3D Guard ring method is not good for sensor selection
- Consistent measurement methods between institutions recommended
- Naming system could have been better...

- In summary CNM sensors fulfill the IBL requirements:
 - ✓ **Good electrical behaviour**
 - ✓ **Good resolution and efficiency**
 - ✓ **Radiation hardness**
 - ✓ **Very stable performance**

Thank you for your attention

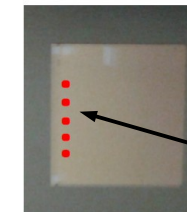
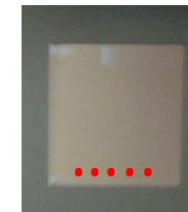
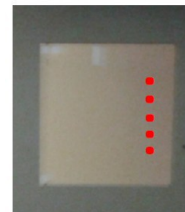
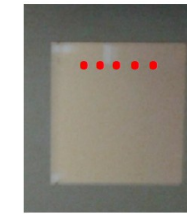
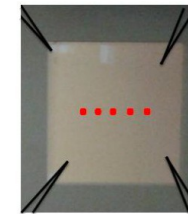
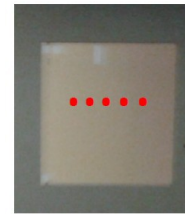
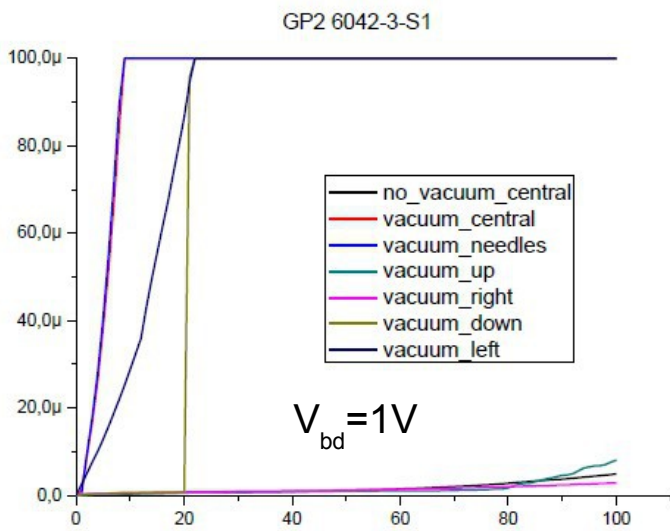
Back up



2 options

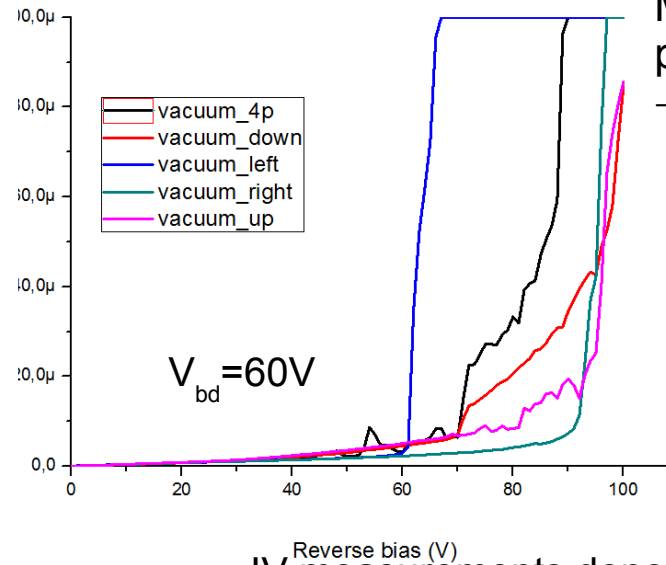
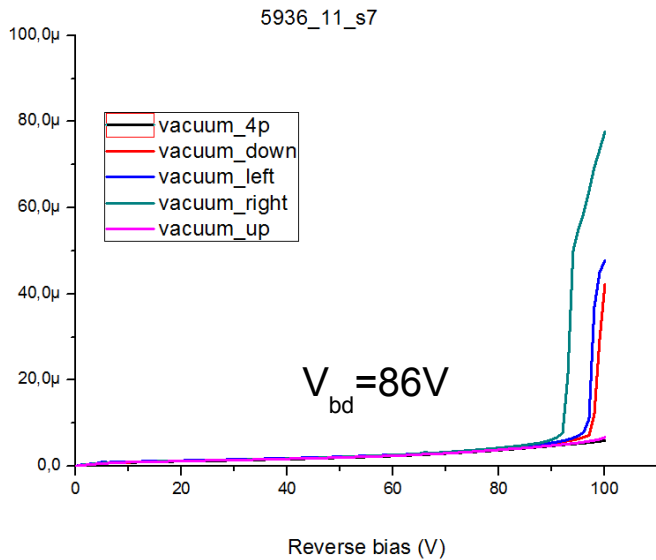
- Measure only one position [vacuum central] (method1)
- Measure ALL positions, take lowest V_{bd} (method2)





Vacuum holes

5936_4_s8



Measure IV with sensor on different positions
 → Take the lowest V_{bd}

IV measurements done by **Sergi Esteban (CNM)**